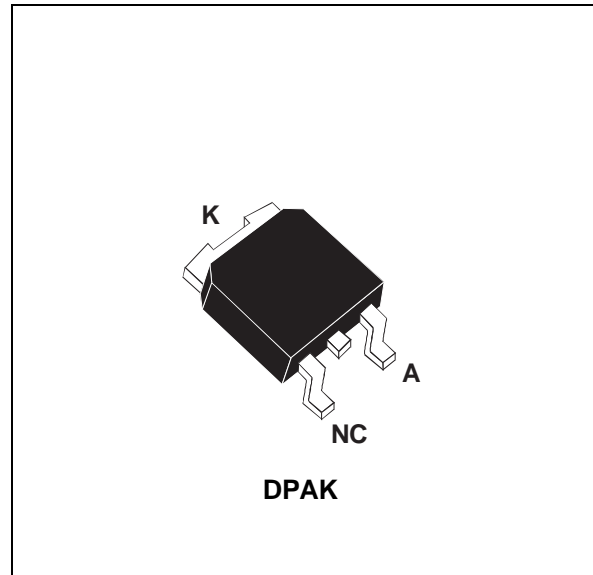


**TURBOSWITCH™ ULTRA-FAST HIGH VOLTAGE DIODE**
**MAIN PRODUCT CHARACTERISTICS**

<b>I<sub>F(AV)</sub></b>	<b>3 A</b>
<b>V<sub>RRM</sub></b>	<b>1200 V</b>
<b>t<sub>rr</sub> (typ)</b>	<b>65 ns</b>
<b>V<sub>F</sub> (max)</b>	<b>1.7 V</b>

**FEATURES AND BENEFITS**

- SPECIFIC TO THE FOLLOWING OPERATIONS :  
SNUBBING OR CLAMPING, DEMAGNETIZATION AND RECTIFICATION
- ULTRA-FAST, SOFT RECOVERY
- VERY LOW OVERALL POWER LOSSES AND PARTICULARLY LOW FORWARD VOLTAGE
- HIGH FREQUENCY OPERATION
- HIGH REVERSE VOLTAGE CAPABILITY


**DESCRIPTION**

TURBOSWITCH 1200V drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes.

Due to their optimized switching performances they also highly decrease power losses in any associated switching IGBT or MOSFET in all "freewheel mode" operations.

They are particularly suitable in motor control circuitries, or in primary of SMPS as snubber, clamping or demagnetizing diodes. They are also suitable for the secondary of SMPS as high voltage rectifier diodes.

**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage		1200	V
V <sub>RSM</sub>	Non repetitive peak reverse voltage		1200	V
I <sub>F(RMS)</sub>	RMS forward current		6	A
I <sub>FRM</sub>	Repetitive peak forward current	tp = 5 μs F = 5kHz square	35	A
I <sub>FSM</sub>	Surge non repetitive forward current	tp = 10ms sinusoidal	25	A
T <sub>stg</sub>	Storage temperature range		- 65 to + 150	°C
T <sub>j</sub>	Maximum operating junction temperature		125	°C

## STTA312B

### THERMAL AND POWER DATA

Symbol	Parameter	Tests conditions	Value	Unit
$R_{th(j-c)}$	Junction to case thermal resistance		6.5	°C/W
$P_1$	Conduction power dissipation	$I_{F(AV)} = 3A, \delta = 0.5$ $T_c = 80^\circ C$	6.7	W
$P_{max}$	Total power dissipation $P_{max} = P_1 + P_3$ ( $P_3 = 10\% P_1$ )	$T_c = 76^\circ C$	7.5	W

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions	Min.	Typ.	Max.	Unit
$V_F^{**}$	Forward voltage drop	$I_F = 3A$ $T_j = 25^\circ C$			1.8	V
		$I_F = 3A$ $T_j = 125^\circ C$		1.15	1.7	
$I_R^*$	Reverse leakage current	$V_R = 0.8$ $\times V_{RRM}$	$T_j = 25^\circ C$		20	$\mu A$
			$T_j = 125^\circ C$		150	400
$V_{to}$	Threshold voltage	$I_p < 3.I_{AV}$ $T_j = 125^\circ C$			1.15	V
$r_d$	Dynamic resistance				185	m $\Omega$

Test pulses : \*  $t_p = 380 \mu s, \delta < 2\%$   
\*\*  $t_p = 5 ms, \delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = V_{to} \times I_{F(AV)} + r_d \times I_{F(RMS)}^2$$

### DYNAMIC ELECTRICAL CHARACTERISTICS

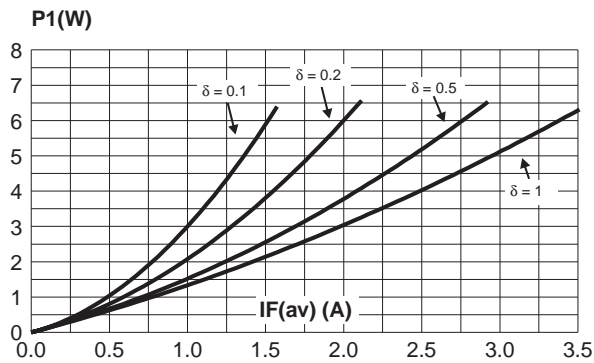
#### TURN-OFF SWITCHING

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$		$T_j = 25^\circ C$ $I_F = 0.5A$ $I_R = 1A$ $I_{rr} = 0.25A$ $I_F = 1A$ $di_F/dt = 50A/\mu s$ $V_R = 30V$		65	115	ns
$I_{RM}$	Maximum recovery current	$T_j = 125^\circ C$ $I_F = 3A$ $V_R = 600V$ $di_F/dt = -16A/\mu s$ $di_F/dt = -50A/\mu s$		6.0	3.6	A
S factor	Softness factor	$T_j = 125^\circ C$ $V_R = 600V$ $I_F = 3A$ $di_F/dt = -50A/\mu s$		1.2		-

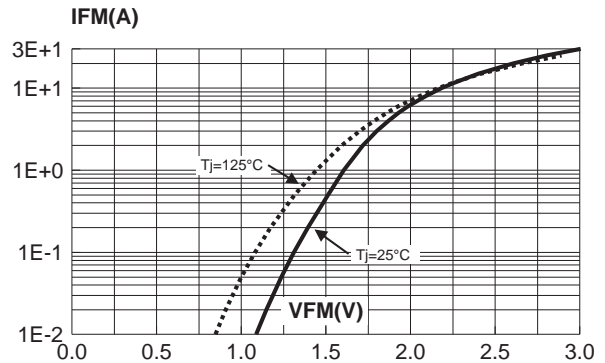
#### TURN-ON SWITCHING

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{fr}$	Forward recovery time	$T_j = 25^\circ C$ $I_F = 3A$ $di_F/dt = 16A/\mu s$ Measured at $1.1 \times V_{Fmax}$			900	ns
$V_{FP}$	Peak forward voltage				35	V

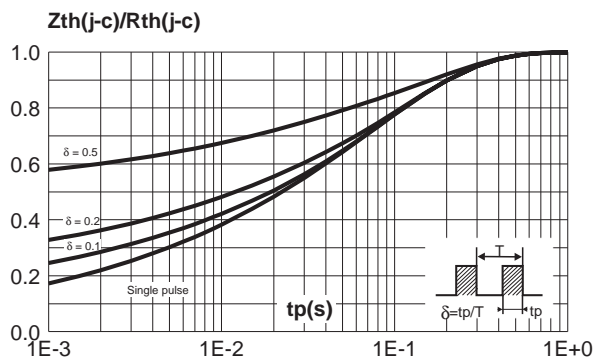
**Fig. 1:** Conduction losses versus average current.



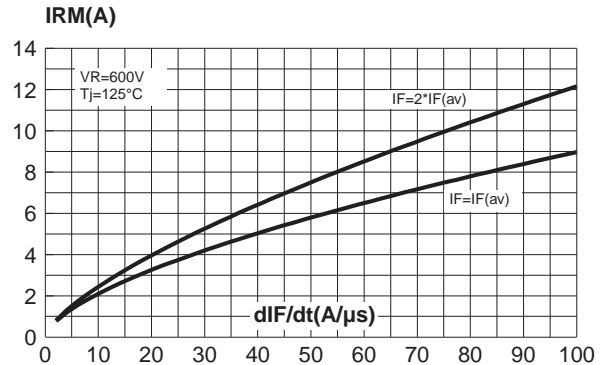
**Fig. 2:** Forward voltage drop versus forward current (maximum values).



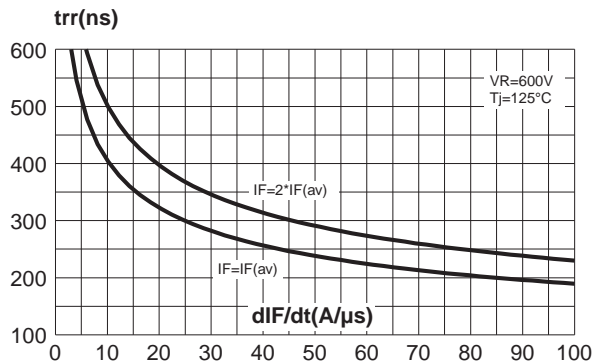
**Fig. 3:** Relative variation of thermal impedance junction to case versus pulse duration.



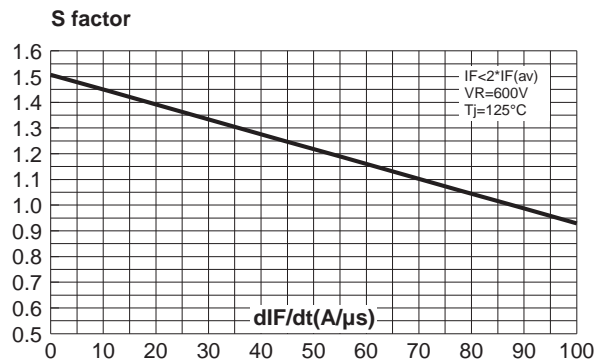
**Fig. 4:** Peak reverse recovery current versus  $dI_F/dt$  (90% confidence).



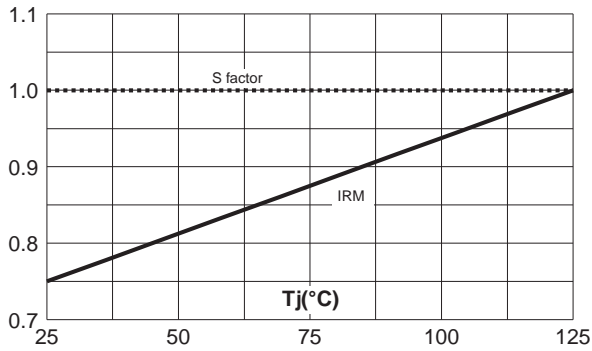
**Fig. 5:** Reverse recovery time versus  $dI_F/dt$  (90% confidence).



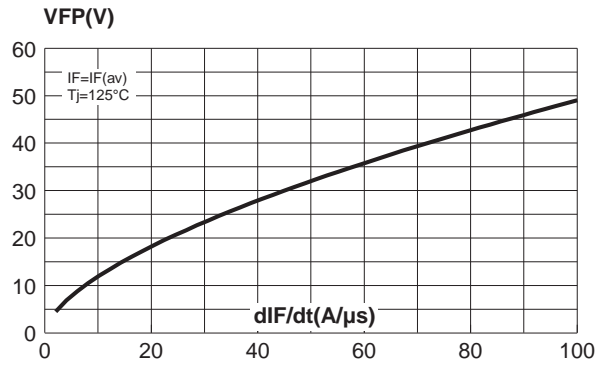
**Fig. 6:** Softness factor  $t_b/t_a$  versus  $dI_F/dt$  (typical values).



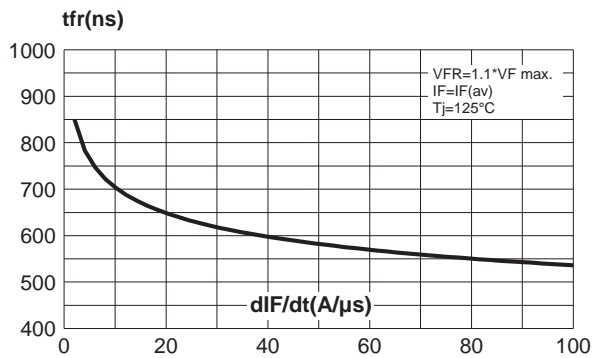
**Fig. 7:** Relative variation of dynamic parameters versus junction temperature (reference:  $T_j=125^\circ\text{C}$ ).



**Fig. 8:** Transient peak forward voltage versus  $dI_F/dt$  (90% confidence).



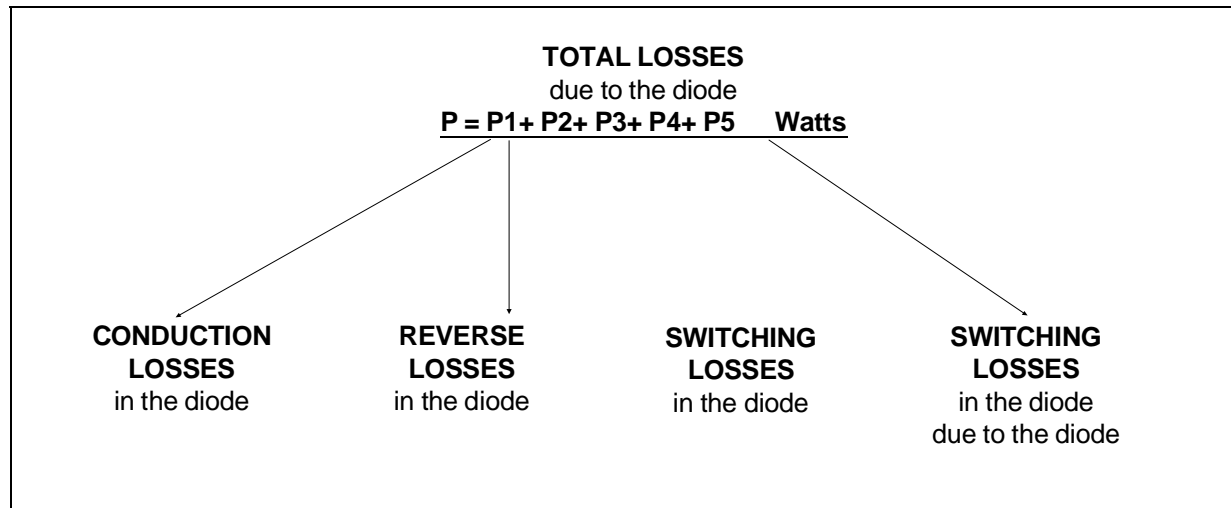
**Fig. 9:** Forward recovery time versus  $dI_F/dt$  (90% confidence).



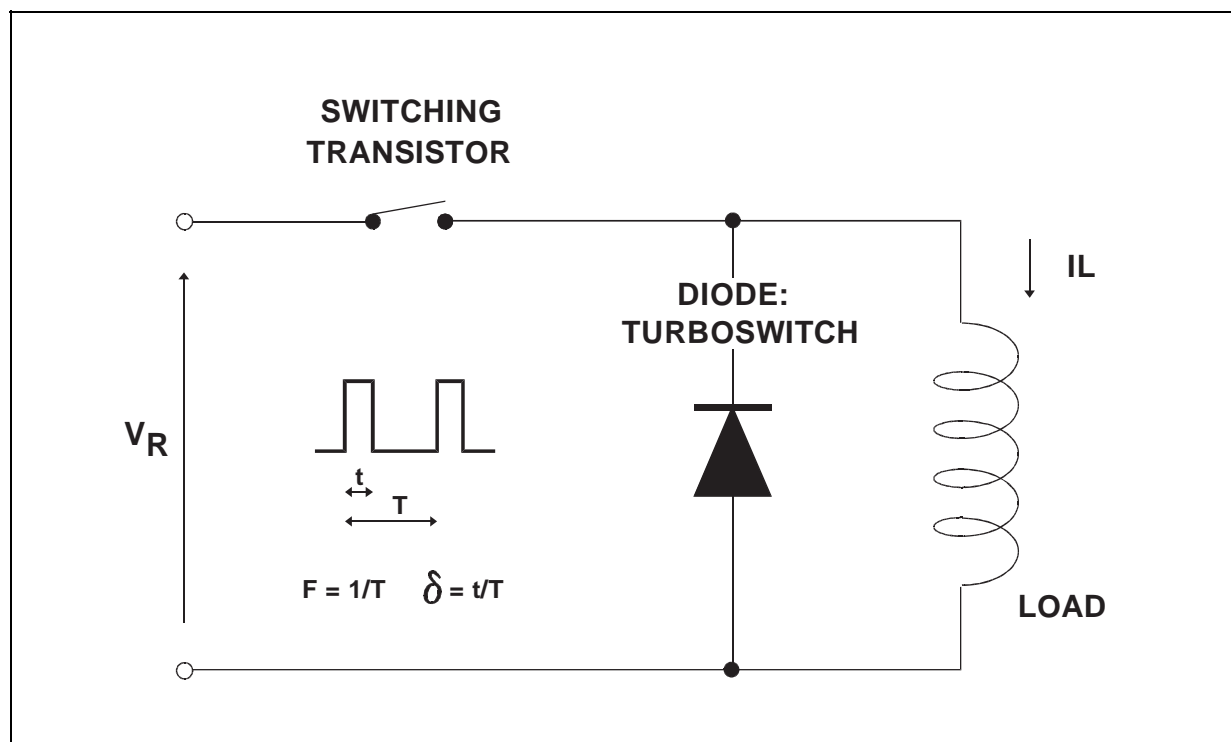
**APPLICATION DATA**

The 1200V TURBOSWITCH™ series has been designed to provide the lowest overall power losses in all frequency or high pulsed current operations.

In such application (fig. A to D), the way of calculating the power losses is given below :



**Fig. A :** "FREEWHEEL MODE".



APPLICATION DATA (Cont'd)

Fig. B : SNUBBER DIODE.

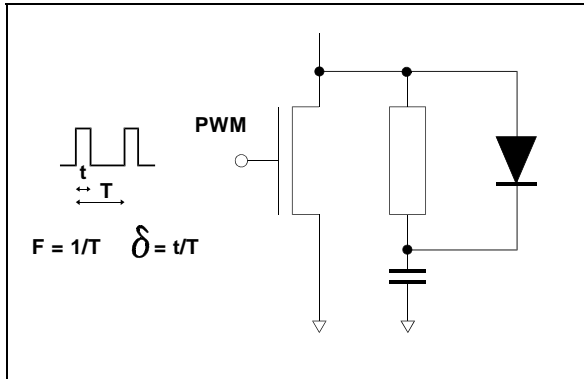


Fig. C : DEMAGNETIZING DIODE.

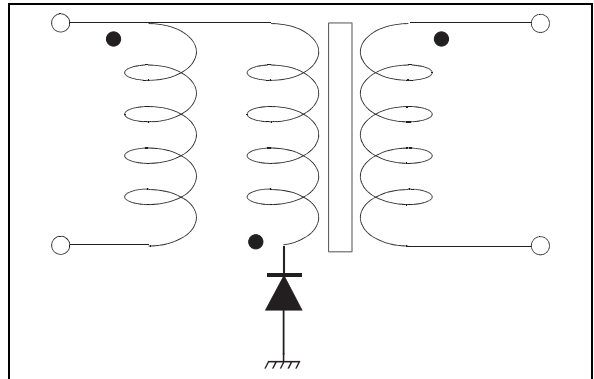


Fig. D : RECTIFIER DIODE.

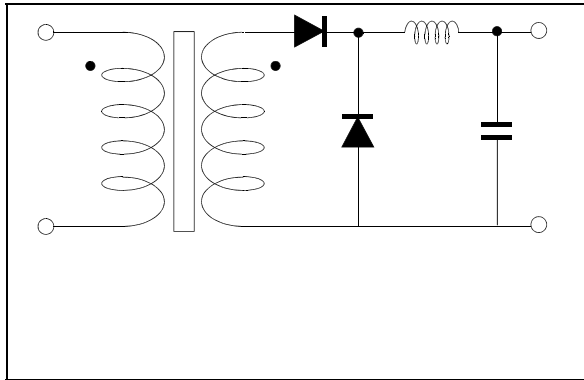
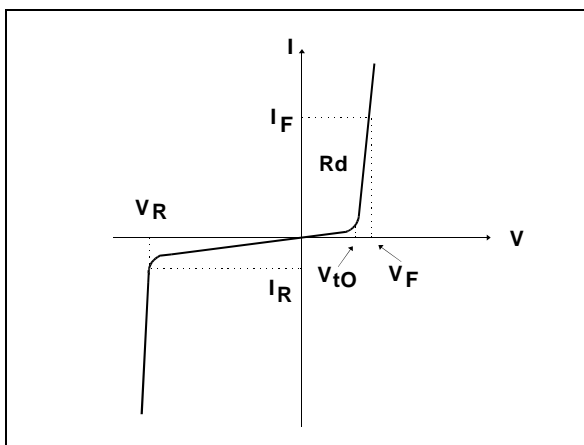


Fig. E : STATIC CHARACTERISTICS.



**Conduction losses :**

$$P1 = V_{t0} \times I_{F(AV)} + R_d \times I_F^2(\text{RMS})$$

**Reverse losses :**

$$P2 = V_R \times I_R \times (1 - \delta)$$

APPLICATION DATA (Cont'd)

Fig. F : TURN-OFF CHARACTERISTICS.

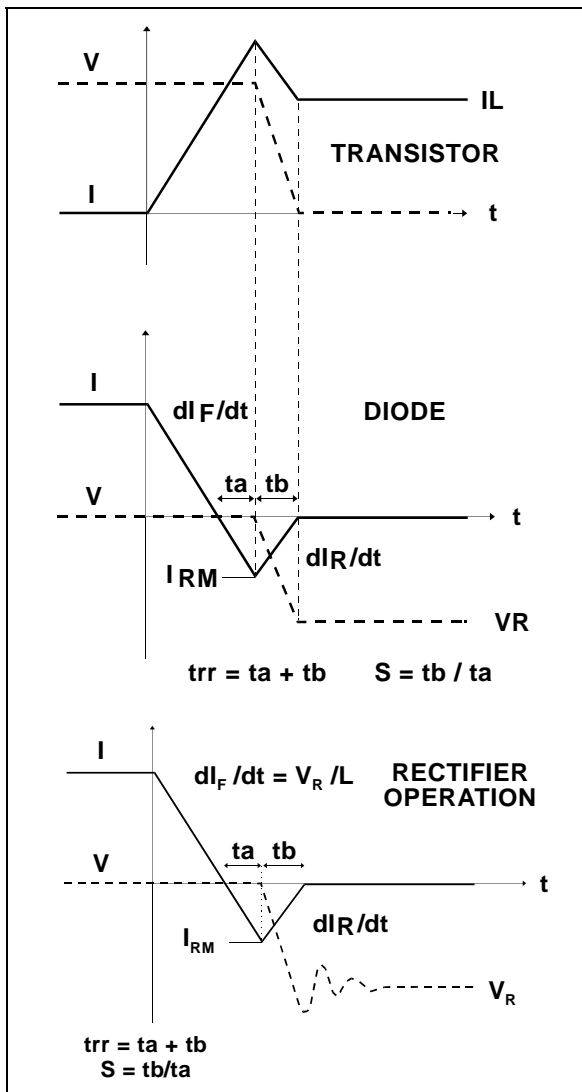
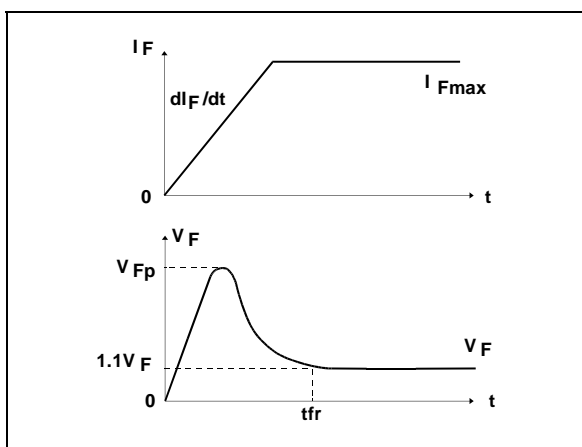


Fig. G : TURN-ON CHARACTERISTICS.



Turn-on losses :  
(in the transistor, due to the diode)

$$P5 = \frac{V_R \times I_{RM}^2 \times (3+2 \times S) F}{6 \times dI_F/dt} + \frac{V_R \times I_{RM} \times I_L \times (S+2) \times F}{2 \times dI_F/dt}$$

Turn-off losses :

$$P3 = \frac{V_R \times I_{RM}^2 \times S \times F}{6 \times dI_F/dt}$$

Turn-off losses :  
with non negligible serial inductance

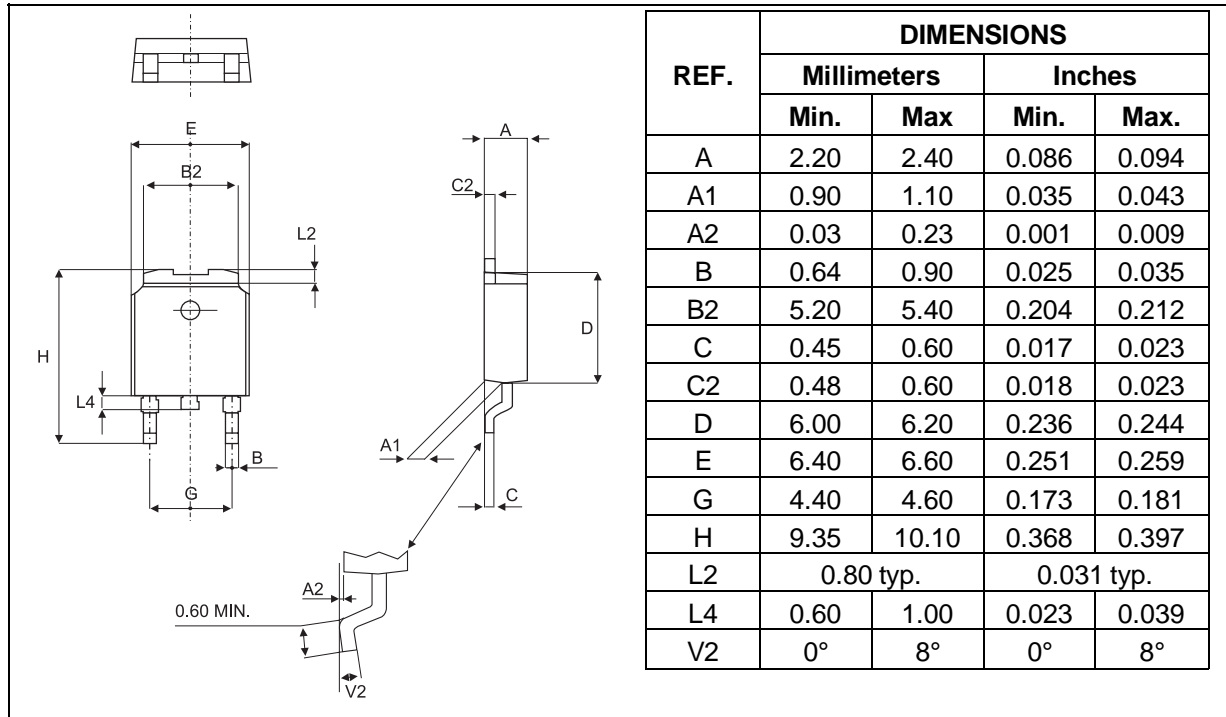
$$P3' = \frac{V_R \times I_{RM}^2 \times S \times F \times L \times I_{RM}^2 \times F}{6 \times dI_F/dt + 2}$$

P3, P3' and P5 are suitable for power MOSFET and IGBT

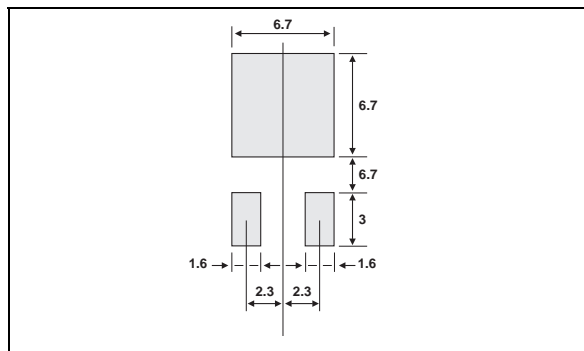
Turn-on losses :  
 $P4 = 0.4 (V_{FP} - V_F) \times I_{Fmax} \times t_{fr} \times F$

# STTA312B

## PACKAGE MECHANICAL DATA DPAK



### FOOTPRINT DIMENSIONS (in millimeters)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTA312B	A312	DPAK	0.3g	75	Tube
STTA312B-TR	A312	DPAK	0.3g	2500	Tape & reel

■ Epoxy meets UL94,V0

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